

PATENT**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:

HARTMUT RUELKE
JOERG HOHAGE
THOMAS WERNER
MICHAEL KIENE

Examiner: Thanhha S. Pham

Group Art Unit: 2813

Att'y Docket: 2000.108700/DE0363

Customer No.: 23720

Serial No.: 10/716,681

Filed: November 19, 2003

For: NITROGEN-ENRICHED LOW-K
BARRIER LAYER FOR A COPPER
METALLIZATION LAYER

RESPONSE TO COMMUNICATION FROM EXAMINER

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

CERTIFICATE OF TRANSMISSION

I hereby certify that this correspondence is being facsimile
transmitted to the Patents and Trademark Office, Washington
D.C., 20231, on the date below.

December 5, 2005


SIGNATURE

Sir:

This paper is submitted in response to a communication from Examiner Pham on
December 5, 2005.

No fees are believed to be due in connection with the present paper. However, should
any fees be required under 37 C.F.R. §§ 1.16 to 1.21, the Director is authorized to deduct such
fees from the Advanced Micro Devices, Inc. Deposit Account No. 01-0365/DE0363.¹

Reconsideration of the application in view of the following amendments and remarks is
respectfully requested.

¹ In the event the monies in that account are insufficient, the Director is authorized to withdraw funds from
Williams, Morgan & Amerson, P.C. Deposit Account No. 50-0786/108700.